NSN 5962-00-434-3135

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Body Outside Diameter: 0.550 inches Body Height:

Between 0.050 inches and 0.070 inches

Maximum Power Dissipation Rating:

150.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Monolithic and hermetically sealed and w/enable

Inclosure Material:

Glass and metal

Inclosure Configuration:

Flat pack

Output Logic Form:

P-type metal oxide-semiconductor logic

Input Circuit Pattern:

2 input

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

0.3 volts power source

Time Rating Per Chacteristic:

80.00 nanoseconds propagation delay time, low to high level output and 80.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Precious Material And Location:

Terminal and top and bottom pkg surfaces gold

Precious Material:

Gold

Test Data Document:

13499-351-8102 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

22 flat leads

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

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